



### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	28mΩ @ V <sub>GS</sub> = 4.5V	7.63A
20V	41mΩ @ V <sub>GS</sub> = 2.5V	4.35A

### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Power Management Functions
- DC-DC Converters

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)

SO-8

8 D1 7 D1

6 D2

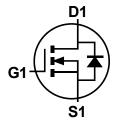


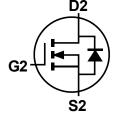
G2 4 5 D2

TOP VIEW

Internal Schematic

G1 2 S2 3





N-Channel MOSFET

N-Channel MOSFET

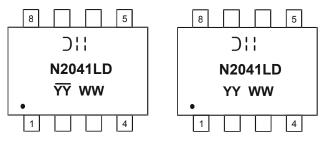
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041LSD-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Chengdu A/T Site Shanghai A/T Site

O':| = Manufacturer's Marking
N2041LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	ID	7.63 4.92	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	30	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.16	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	R <sub>0JA</sub>	107.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

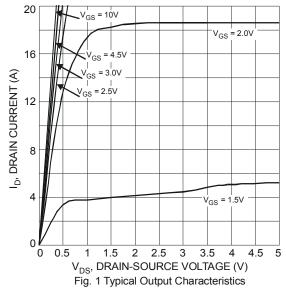
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

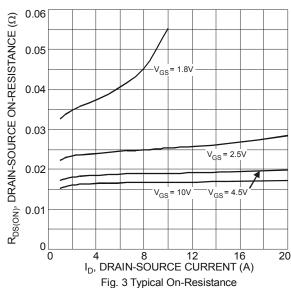
Characteristic Symbol Min Typ Max Unit Test Condition							
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	l	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.2	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D		19	28	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Static Dialii-Source Off-Resistance	R <sub>DS</sub> (ON)		25	41		$V_{GS} = 2.5V, I_D = 5.2A$	
Forward Transfer Admittance	Y <sub>fs</sub>		6		S	$V_{DS} = 10V, I_{D} = 6A$	
Diode Forward Voltage	$V_{SD}$	l	0.7	1.2	<b>V</b>	$V_{GS} = 0V, I_{S} = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	l	550			10)()(	
Output Capacitance	Coss	l	88		pF	$V_{DS}$ =10V, $V_{GS}$ = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	l	81			1 - 1101112	
Gate Resistance	Rg	l	1.34		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	l	15.6		nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$	
Total Gate Charge	Qg	l	7.2		45777 407		
Gate-Source Charge	Qgs	_	1	_	nC	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V},$	
Gate-Drain Charge	Q <sub>gd</sub>	_	1.9	_		I <sub>D</sub> = 6A	
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.69	_			
Turn-On Rise Time	t <sub>r</sub>	-	13.19	_	20	$V_{DD} = 10V, V_{GEN} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	1	22.1	_	ns $R_g = 1\Omega$ , $I_D = 6.7A$		
Turn-Off Fall Time	t <sub>f</sub>	_	6.43	_			

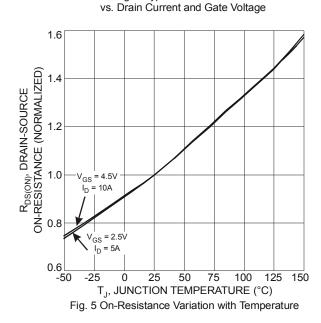
Notes:

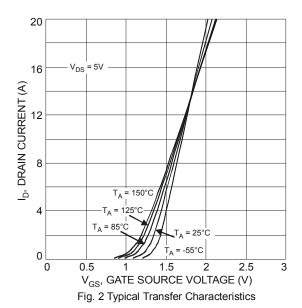
- Device mounted on FR-4 PCB with minimum recommended pad layout.
   Repetitive rating, pulse width limited by function temperature.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to production testing.











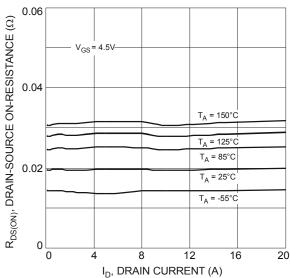


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

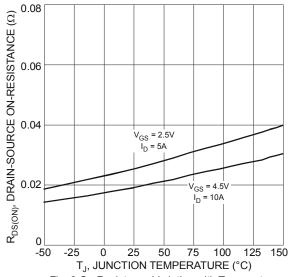


Fig. 6 On-Resistance Variation with Temperature



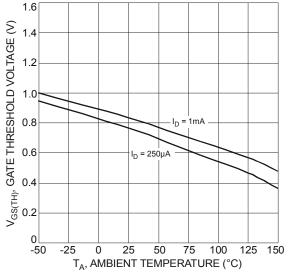
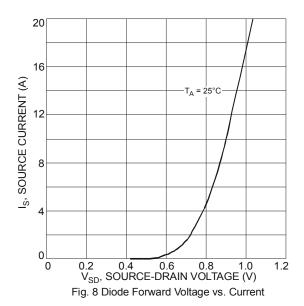
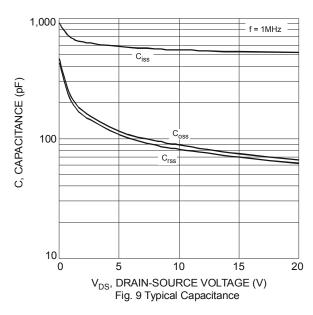
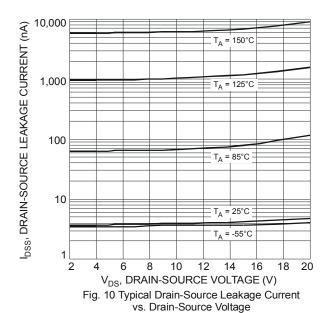


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







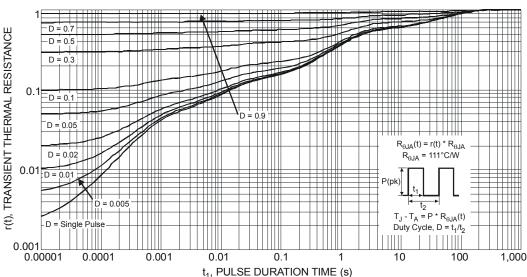
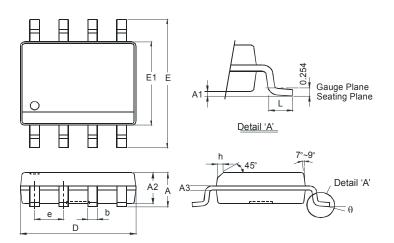


Fig. 11 Transient Thermal Response



## **Package Outline Dimensions**

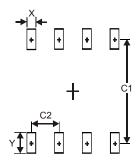
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
E	5.90	6.10		
E1	3.85	3.95		
е	<b>e</b> 1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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